



100V NPN MEDIUM POWER TRANSISTOR IN SOT89

Features

- BV_{CEO} > 100V
- BV_{ECO} > 6V
- I_C = 2.5A Continuous Collector Current
- I_{CM} = 3.5A Peak Collector Current
- V_{CE(SAT)} < 100mV @ 1A
- $R_{CE(SAT)} = 80m\Omega$ for a Low Equivalent On-Resistance
- Complementary PNP Type: ZXTP25100CZ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

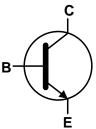
Case: SOT89

- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.05 grams (Approximate)

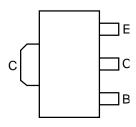
SOT89







Device Symbol



Top View Pin Out

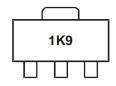
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXTN25100DZTA	AEC-Q101	1K9	7	12	1,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



1K9 = Product Type Marking Code



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEX}	180	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	6	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	2.5	Α
Peak Pulse Current	I _{CM}	3.5	Α
Base Current	lΒ	1	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1.1 8.8		
Power Dissipation	(Note 6)	_	1.8 14.4	W mW/°C	
Linear Derating Factor	(Note 7)	P _D	2.4 19.2		
	(Note 8)		4.46 35.7		
	(Note 5)		117	°C/W	
Thermal Decistores, Junction to Ambient Air	(Note 6)	Б	68		
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{ heta JA}$	51		
	(Note 8)		28		
Thermal Resistance, Junction to Lead	(Note 9)	R _{0JL}	7.95		
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

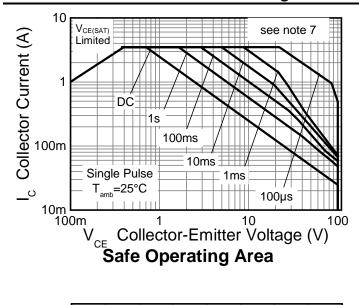
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

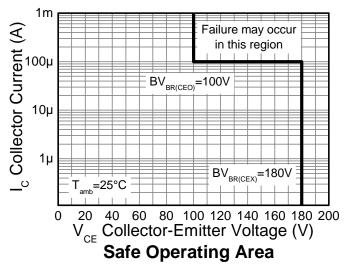
Notes:

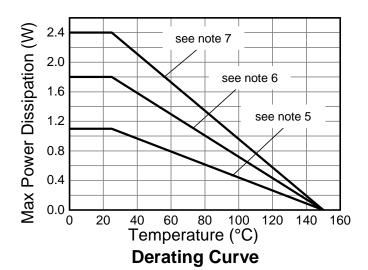
- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 0.6mm FR-4 PCB; device is measured For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copunder still air conditions whilst operating in a steady-state.
 Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
 Same as Note 7, except the device is measured at t<5 seconds.
 Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information

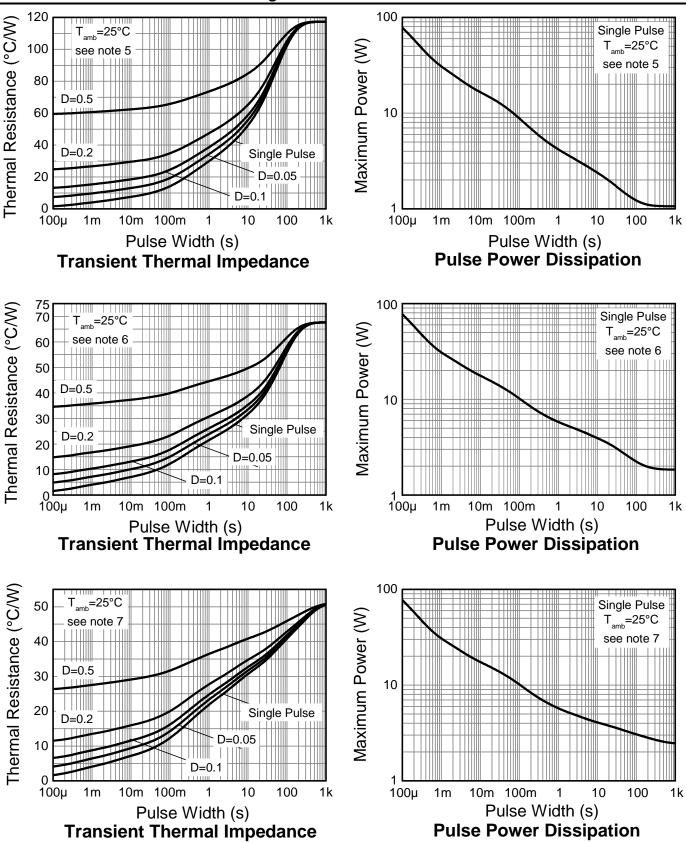








Thermal Characteristics and Derating Information





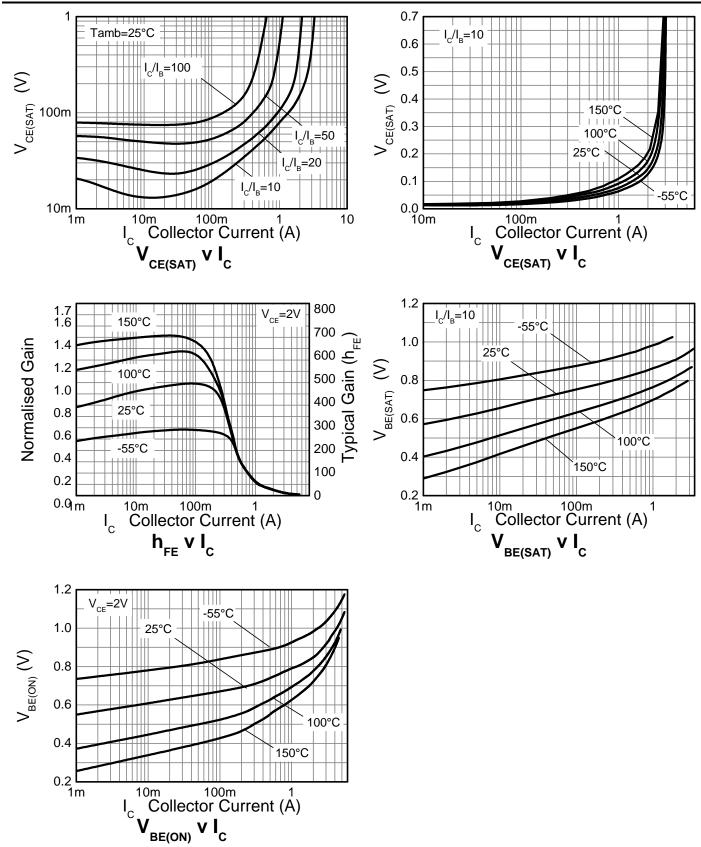
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	180	220	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Forward Blocking)	BV _{CEX}	180	220	_	V	$I_C = 100\mu A, R_{BE} < 1k\Omega \text{ or} -1V > V_{BE} > 0.25V$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	100	130	_	V	$I_C = 10mA$
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV _{ECX}	6	8.2	_	V	$I_E = 100\mu A$, $R_{BC} < 1k\Omega$ or $0.25V > V_{BC} > -0.25V$
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV _{ECO}	6	8.7	_	V	I _E = 100μA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.3	_	V	$I_E = 100\mu A$
Collector-Base Cutoff Current	I _{CBO}		<1	50 0.5	nA μA	V _{CB} = 180V V _{CB} = 180V, T _A = +100°C
Collector-Emitter Cutoff Current	I _{CEX}	_	_	100	nA	$V_{CE} = 100V, R_{BE} < 1k\Omega \text{ or}$ $1V < V_{BE} < 0.25V$
Emitter Cutoff Current	I _{EBO}	_	<1	50	nA	$V_{EB} = 5.6V$
DC Current Transfer Static Ratio (Note 11)	h _{FE}	300 120 40 —	450 170 60 20	900 — — —	_	$I_{C} = 10\text{mA}, V_{CE} = 2V$ $I_{C} = 0.5\text{A}, V_{CE} = 2V$ $I_{C} = 1\text{A}, V_{CE} = 2V$ $I_{C} = 2.5\text{A}, V_{CE} = 2V$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(SAT)}	-	120 80 220	170 100 345	mV	$I_C = 0.5A$, $I_B = 10mA$ $I_C = 1A$, $I_B = 100mA$ $I_C = 2.5A$, $I_B = 250mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(SAT)}$	ı	935	1000	mV	$I_C = 2.5A$, $I_B = 250mA$
Base-Emitter Turn-on Voltage (Note 11)	V _{BE(ON)}	1	890	950	mV	$I_C = 2.5A, V_{CE} = 2V$
Transitional Frequency	f_{T}	_	175	_	MHz	I _E = 50mA, V _{CE} = 10V f = 100MHz
Input Capacitance	C _{IBO}		154	250	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{OBO}	-	8.7	15	pF	V _{CB} = 10V, f = 1MHz
Delay Time	t _D		16.4	_	ns	
Rise Time	t _R	_	115		ns	$I_C = 500$ mA, $V_{CC} = 10$ V,
Storage Time	t _S		763	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$
Fall Time	t _F		158	_	ns	

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

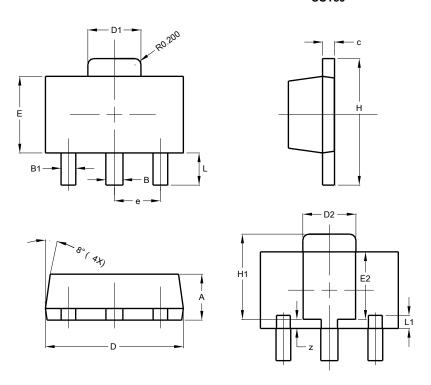




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89

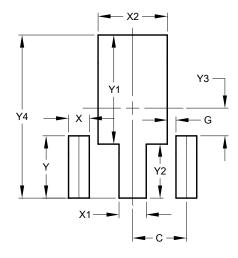


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	1	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value (in mm)		
С	1.500		
G	0.244		
Χ	0.580		
X1	0.760		
X2	1.933		
Υ	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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